

Features

- Halogen Free. "Green" Device (Note 1)
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

Maximum Ratings @ 25°C Unless Otherwise Specified

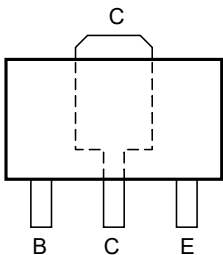
- Operating Junction Temperature Range: -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 250°C/W Junction to Ambient

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	75	V
Collector-Emitter Voltage	V_{CEO}	40	V
Emitter-Base Voltage	V_{EBO}	6	V
Maximum Collector Current	I_{CM}	0.6	A
Collector Power Dissipation	P_C	500	mW

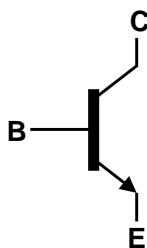
Note: 1. Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

Marking: 1P

Pin Configuration - Top View

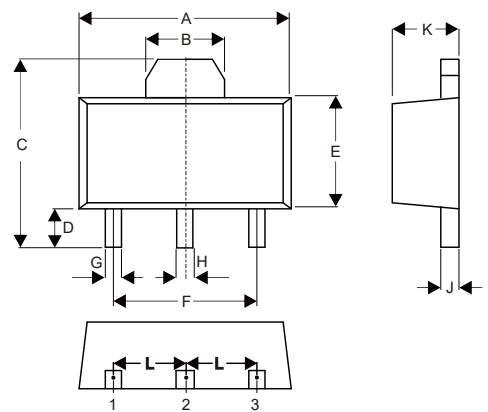


Internal Structure



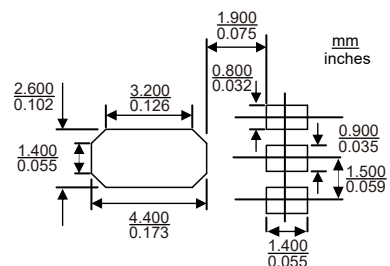
**NPN
General Purpose
Amplifier**

SOT-89



DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	0.169	0.185	4.30	4.70	
B	0.061		1.55		TYP.
C	0.154	0.171	3.91	4.35	
D	0.031	0.047	0.80	1.20	
E	0.089	0.104	2.25	2.65	
F	0.118		3.00		TYP.
G	0.013	0.020	0.33	0.52	
H	0.015	0.021	0.38	0.53	
J	0.014	0.017	0.35	0.44	
K	0.055	0.063	1.40	1.60	
L	0.059		1.50		TYP.

Suggested Solder Pad Layout



Electrical Characteristics @ 25°C Unless Otherwise Specified

Parameter	Symbol	Min	Typ	Max	Units	Conditions
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	75			V	$I_C=10\mu A, I_E=0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	40			V	$I_C=10mA, I_B=0$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	6			V	$I_E=10\mu A, I_C=0$
Base Cutoff Current	I_{BL}			20	nA	$V_{CE}=60V, V_{BE}=-3V$
Collector Cutoff Current	I_{CEX}			10	nA	$V_{CE}=60V, V_{BE}=-3V$
DC Current Gain (Note2)	h_{FE1}	35				$V_{CE}=10V, I_C=0.1mA$
	h_{FE2}	50				$V_{CE}=10V, I_C=1mA$
	h_{FE3}	75				$V_{CE}=10V, I_C=10mA$
	h_{FE4}	100		300		$V_{CE}=10V, I_C=150mA$
	h_{FE5}	50				$V_{CE}=1V, I_C=150mA$
	h_{FE6}	40				$V_{CE}=10V, I_C=500mA$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			0.3	V	$I_C=150mA, I_B=15mA$
				1.0	V	$I_C=500mA, I_B=50mA$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	0.6		1.2	V	$I_C=150mA, I_B=15mA$
				2.0	V	$I_C=500mA, I_B=50mA$
Transition Frequency	f_T	300			MHz	$V_{CE}=20V, I_C=20mA, f=100MHz$
Output Capacitance	C_{obo}			8	pF	$V_{CB}=10V, I_E=0, f=1MHz,$
input Capacitance	C_{ibo}			25	pF	$V_{BE}=0.5V, I_C=0, f=1MHz,$
Noise Figure	NF			4	dB	$V_{CE}=10V, I_C=100\mu A, f=1kHz, R_S=1k\Omega$
Delay Time	t_d			10	ns	$V_{CC}=30V, V_{BE}=0.5V$
Rise Time	t_r			25	ns	$I_C=150mA, I_{B1}=15mA$
Storage Time	t_s			225	ns	$V_{CC}=30V, I_C=150mA$
Fall Time	t_f			60	ns	$I_{B1}=I_{B2}=15mA$

 Note: 2. Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2.0\%$

Curve Characteristics

Fig. 1 - Static Characteristics

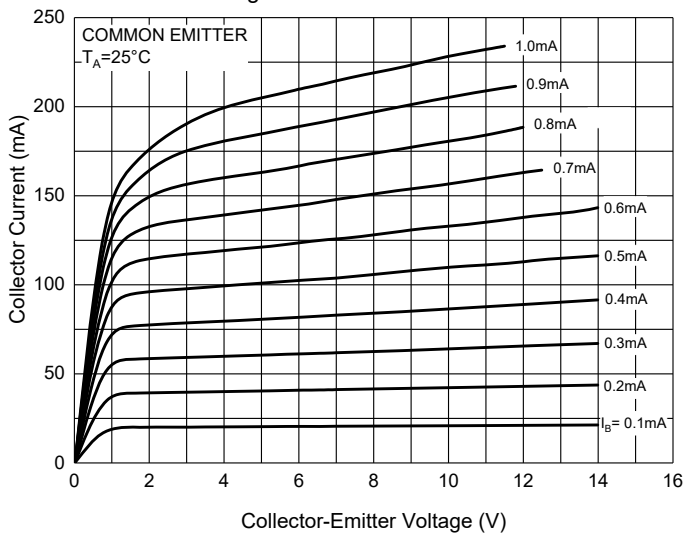


Fig. 2 - DC Current Gain Characteristics

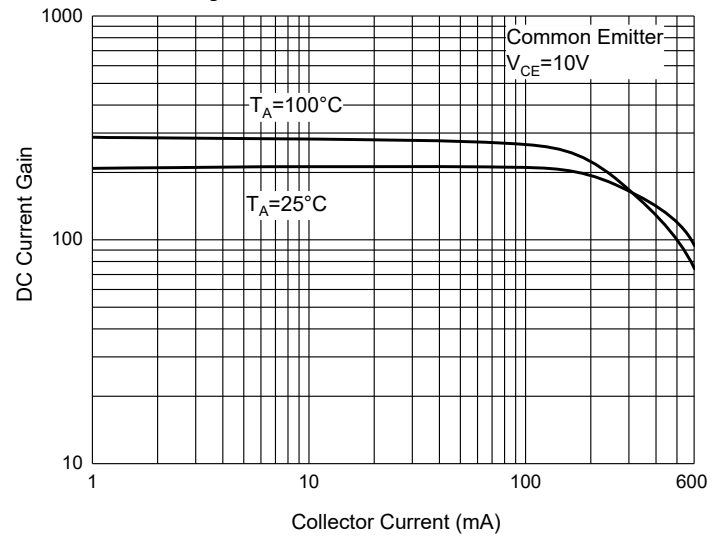


Fig. 3 - Collector-Emitter Saturation Voltage Characteristics

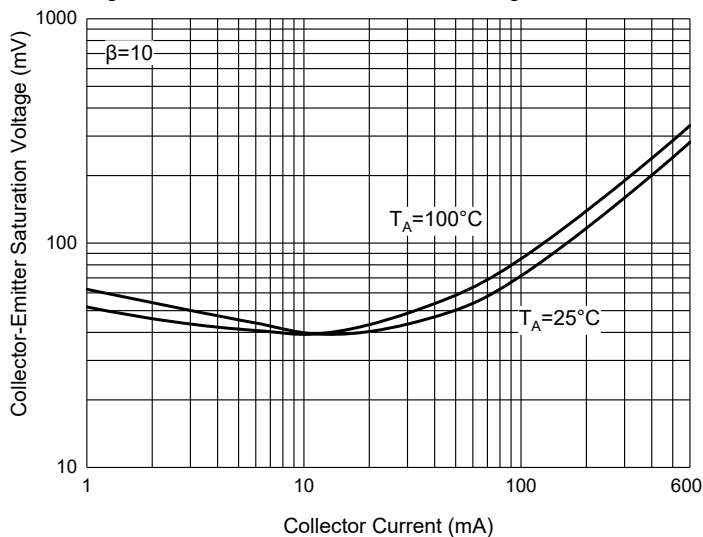


Fig. 4 - Base-Emitter Saturation Voltage Characteristics

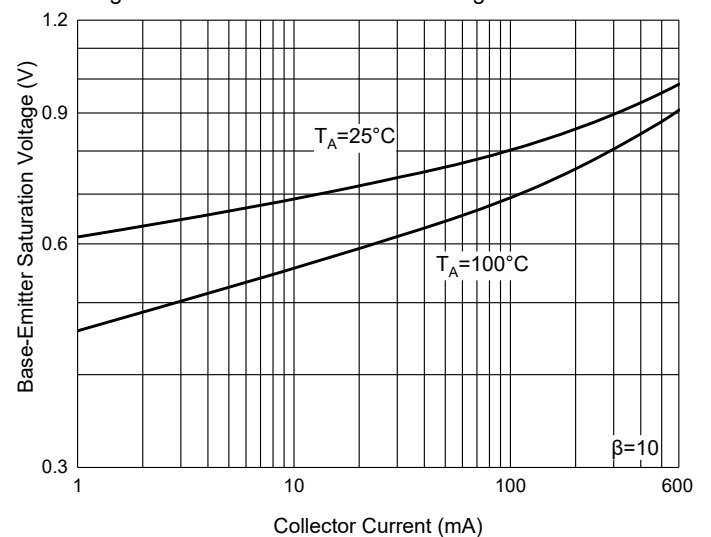


Fig. 5 - Base-Emitter Voltage Characteristics

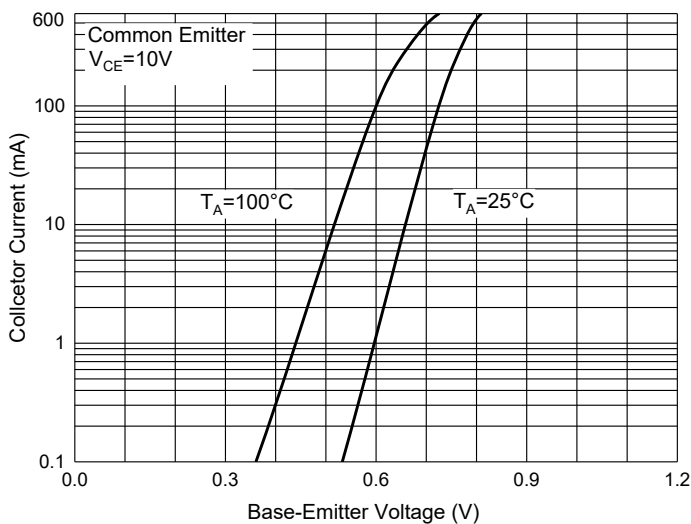


Fig. 6 - Power Derating Curve

